

# Band switching diode

## Features

1. Low differential forward resistance
2. Low diode capacitance
3. High reverse impedance

## Applications

Band switching in VHF-tuners

## Construction

Silicon epitaxial planar

## Absolute Maximum Ratings

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
DC Reverse voltage		$V_R$	35	V
Average rectified current		$I_o$	100	mA
Power dissipation		$P_d$	150	MW
Junction temperature		$T_j$	150	$^{\circ}\text{C}$
Storage temperature range		$T_{stg}$	-55...+150	$^{\circ}\text{C}$

## Maximum Thermal Resistance

$T_j=25^{\circ}\text{C}$

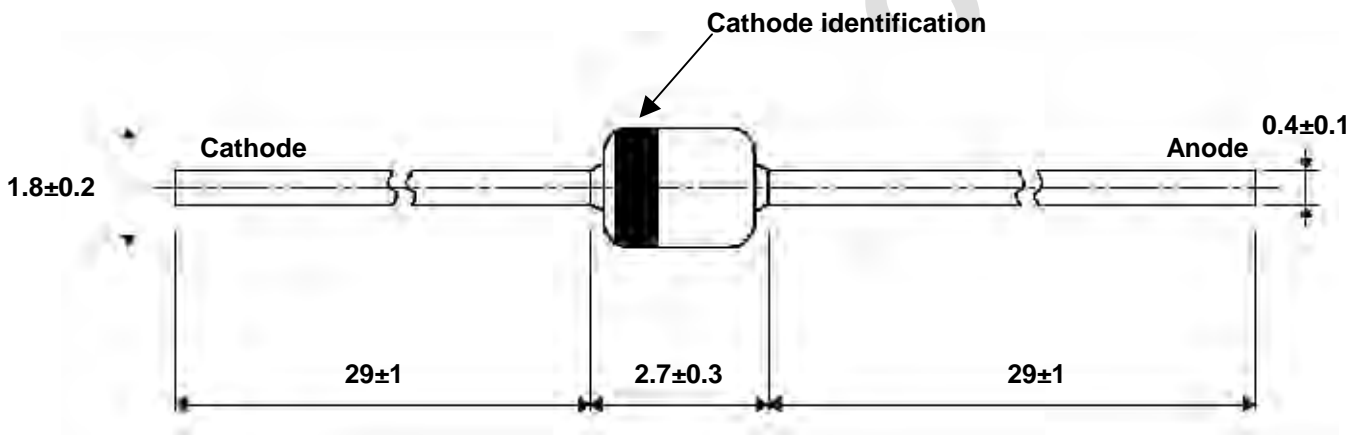
Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	$l=4\text{mm}, T_L=\text{constant}$	$R_{thJA}$	350	K/W

## Electrical Characteristics

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=10\text{mA}$	$V_F$		0.85	1	V
Reverse current	$V_R=20\text{V}$	$I_R$			100	nA
Breakdown voltage	$I_R=10\mu\text{A}$	$B_V$	35			V
Terminal capacitance	$f=1\text{MHz}, V_R=6\text{V}$	$C_t$			1.5	pF
Frequency resistance	$f=100\text{MHz}, I_F=10\text{mA}$	$r_f$			0.6	

## Dimensions in mm



Standard Glass Case  
JEDEC DO 34